

# BRMJD32CQ

Rev.A Apr.-2024

## / Descriptions

KF \$ , ) GE G Silicon PNP transistor in a TO-252 Plastic Package.

## / Features

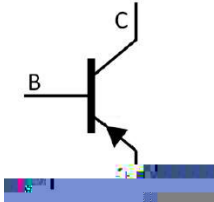
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Low Speed ,Load Formed for Surface Mount Application, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

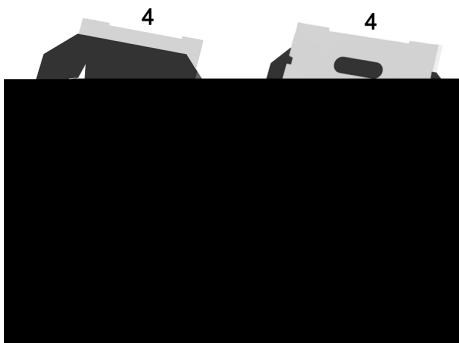
## / Applications

General Purpose Amplifier, Meet the stringent requirements of automotive applications.

## / Equivalent Circuit



## / Pinning



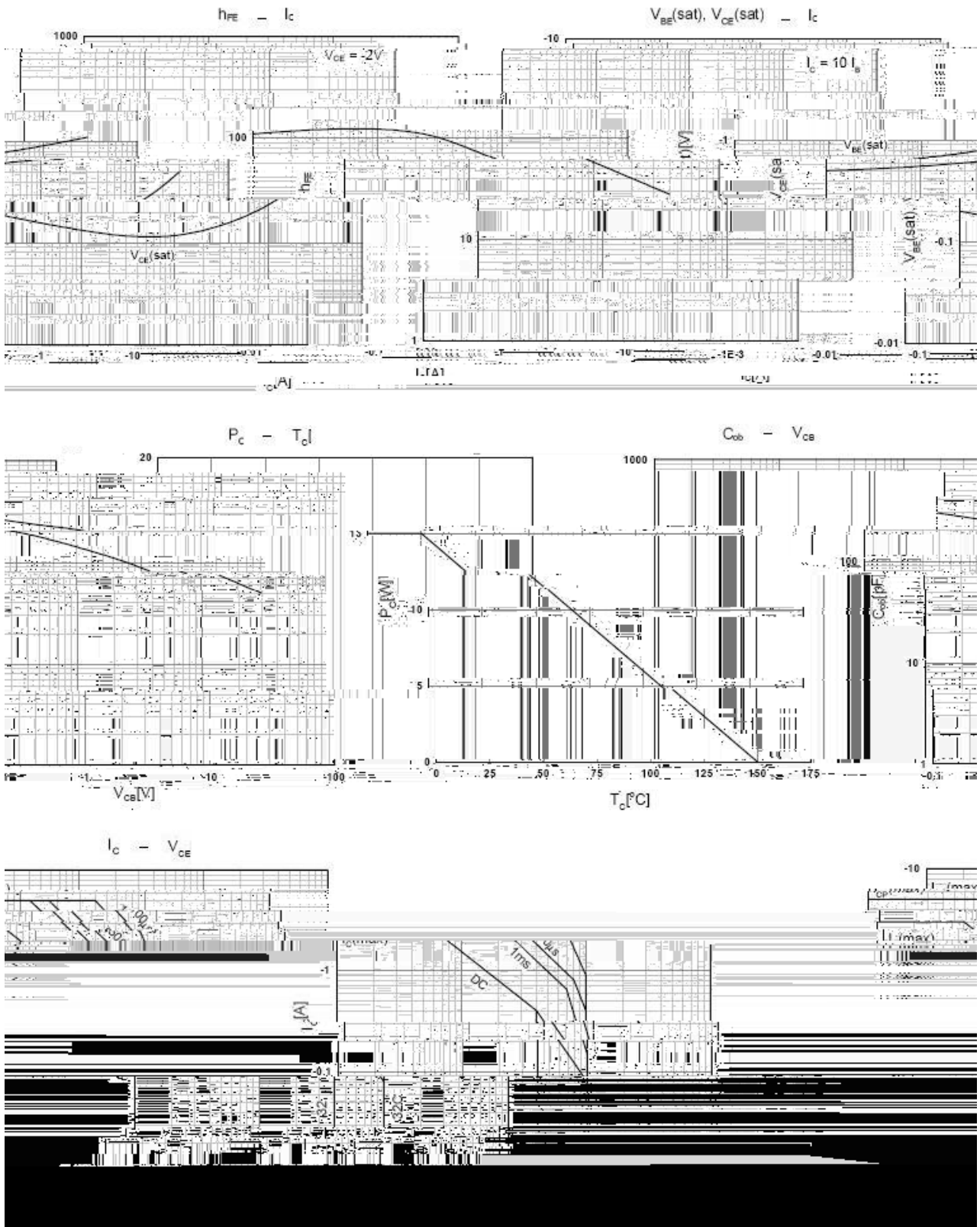
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

## / hFE Classifications & Marking

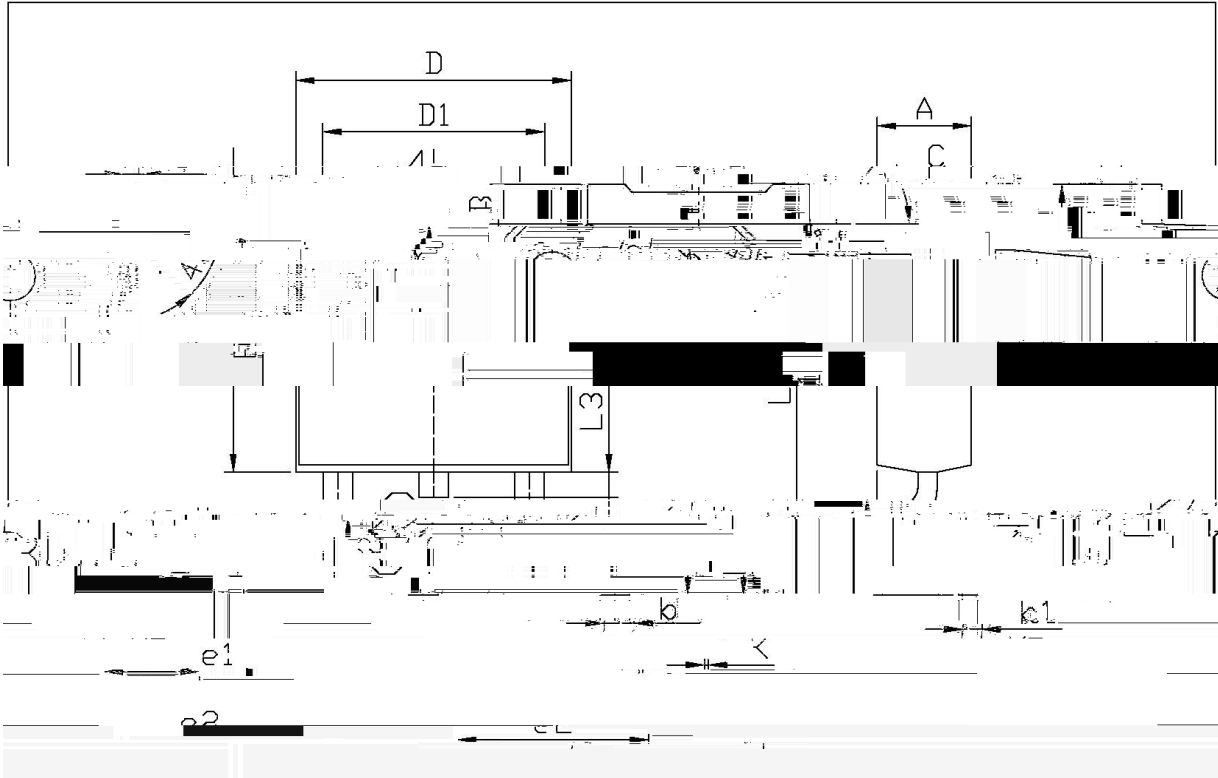
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	-100	V
Collector to Emitter Voltage	$V_{CEO}$	-100	V
Emitter to Base Voltage	$V_{EBO}$	-5.0	V

/ Electrical Characteristic Curve



/ Package Dimensions

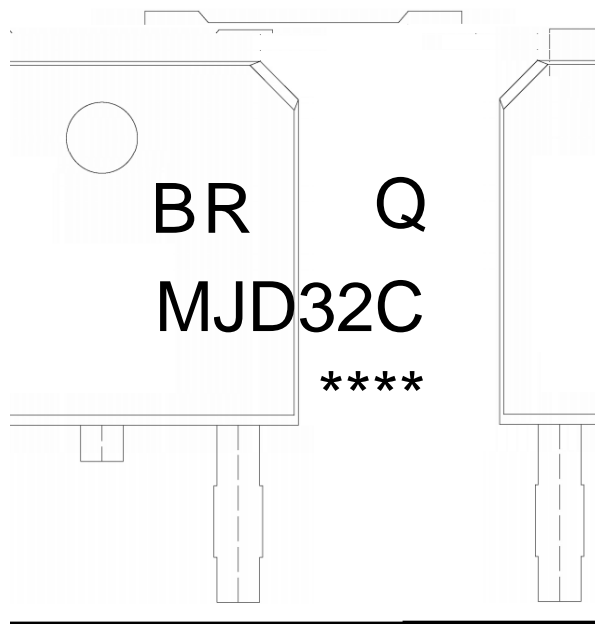


单位: mm

Dimensions, Millimeters		Dimensions In Millimeters	
Min	Max	Symbol	Symbol
		B	2.10
		e1	2.24
		b	0.70
		k1	0.45
		L	1.50
		L3	0.60
		D1	5.10
		D	5.50

T0-252

**/ Marking Instructions**



BR

Q

D A \*):

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Note:

BR: Company Code

Q: Automobile halogen-free product Code

MJD32C: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- 1      150 200      60 120sec;      1.Preheating:150~200 , Time:60~120sec.
- 2      255..5      5..0.5sec;      2.Peak Temp.:255..5 , Duration:5..0.5sec.
- 3      2 10 /sec.      3. Cooling Speed: 2~10 /sec.